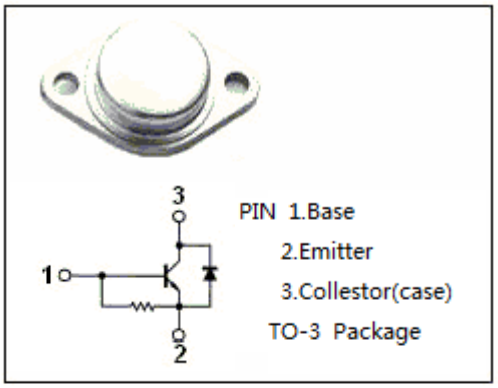
isc Silicon NPN Power Transistor 2SD900

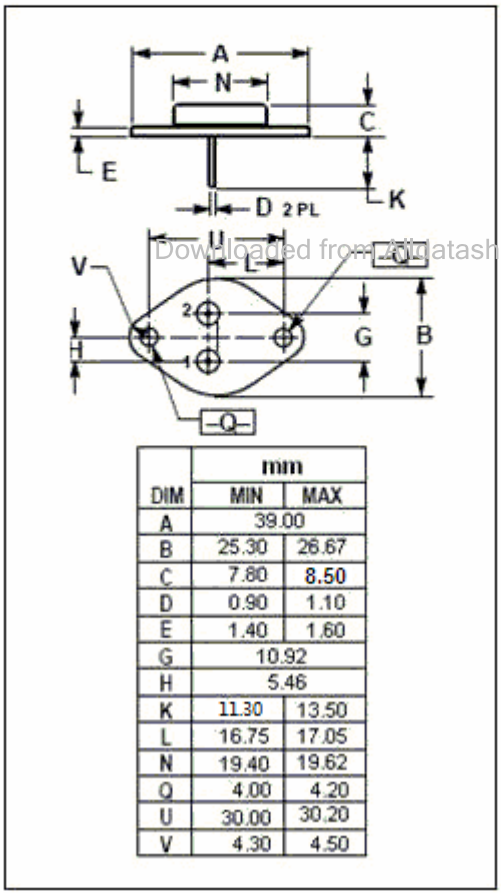


DESCRIPTION

- High Breakdown Voltage-
  : V_{CBO}= 1500V (Min)
- High Switching Speed
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= 5.0V(Max.)@ I_C= 4.5A
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use in color TV deflection circuits.



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector- Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current- Continuous	5	A
I_{CM}	Collector Current- Peak	6	A
P_C	Collector Power Dissipation @ T_C= 25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-45~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{EBO}	Emitter-Base Breakdown Voltage	I_E= 300mA; I_C= 0	6.0			V
I_{CES}	Collector Cutoff Current	V_{CE}= 1500V ; V_{BE}= 0			0.5	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 4.5A; I_B= 1.2A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 4.5A; I_B= 1.2A			1.5	V
h_{FE}	DC Current Gain	I_C= 1A; V_{CE}= 5V	10		40	
V_{ECF}	C-E Diode Forward Voltage	I_F= 6A			3.0	V
t_f	Fall Time	I_C=4A, I_{B1}= 1.1A , I_{B2}= 1.6A			1.0	μ s